# Si Photo Diode Chip--ORT-2160PD

## 1. Scope：

- The specification applies to NIP silicon photo-diode chips.
- Type：ORT-2160PD

## 2. Structure：

- NIP planar type.
- Top（Cathode）Side：aluminum(Al) alloy.
- Back（Anode）Side：silver(Ag) alloy.

## 3. Size：(60mil×60mil)

- Chip size ：(1520μm × 1520μm) ± 40μm
- Chip thickness ：280μm ± 25μm
- Active area ：(1350μm × 1350μm )± 15μm
- Pad size ：(250μm × 250μm) ± 10μm
- Pattern drawing：per fig. 1

## 4. Electro-Optical Characteristics：

(Ta=+25℃)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Forward voltage | $V_F$ | $I_F$=10mA, H=0 | 0.5 | | 1.3 | V |
| Reverse Breakdown voltage | $V_{BR}$ | $I_R$=100μA, H=0 | 35 | | | V |
| Reverse Dark Current | $I_D$ | $V_R$=10V, H=0 | | | 10 | nA |
| Light Current | $I_L$ | $V_R$=5V,Has 1mw/cm$^2$,@ 940nm | | 75 | | μA |
| Peak Sensing wavelength | $\lambda_P$ | | | 940 | | nm |
| Junction Capacitance | $C_J$ | $V_R$=3V, F=1MHz | | 12 | | pF |

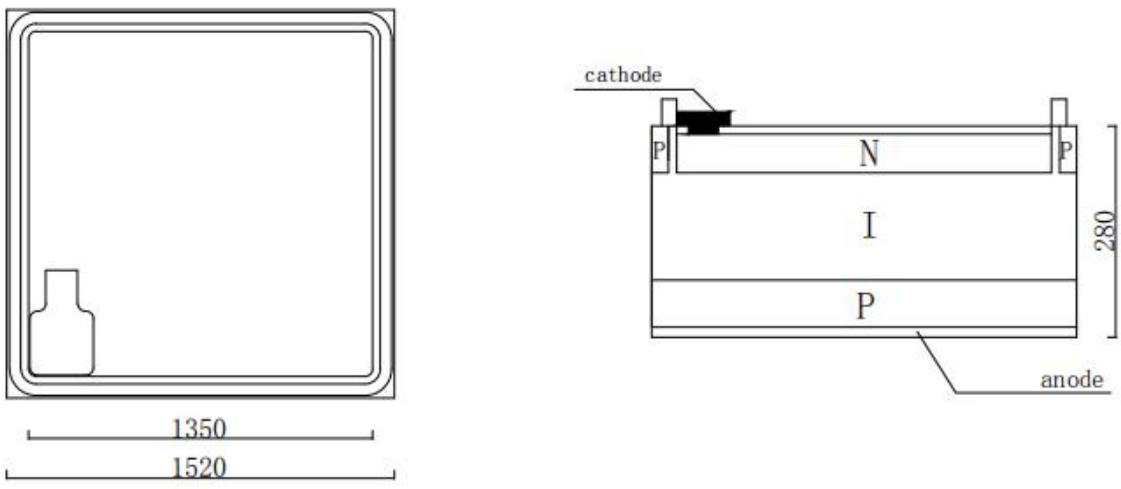


fig.1

## 5. Spectral Response